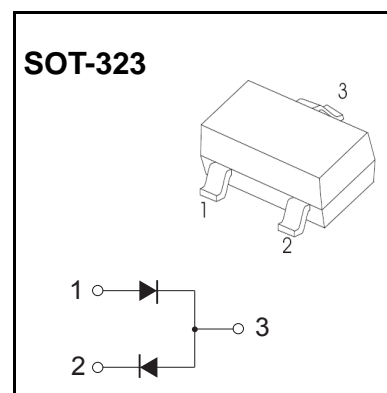


Plastic-Encapsulate Diodes

SWITCHING DIODE

FEATURES

- This Switching Diode has The Following Features:
- Low Leakage Current Applications



Marking:L21

Maximum Ratings @Ta=25°C

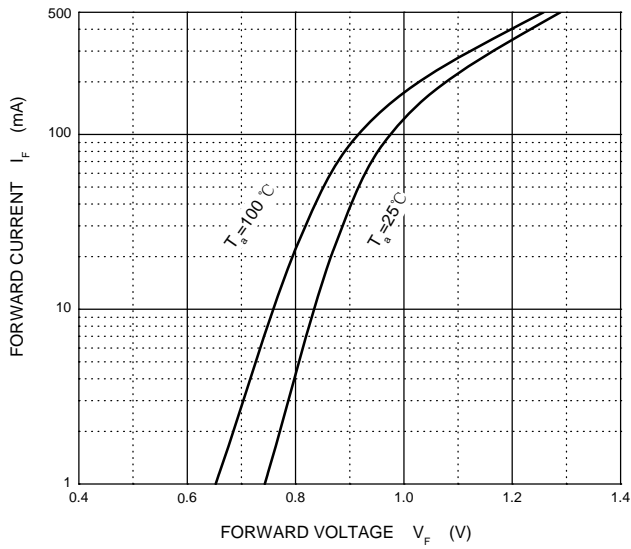
Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	70	V
DC Blocking Voltage	V_R	70	V
Forward Continuous Current	I_{FM}	500	mA
Average Rectified Output Current	I_O	215	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}	1.0	A
Power Dissipation	P_D	200	mW
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{STG}	-55~+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

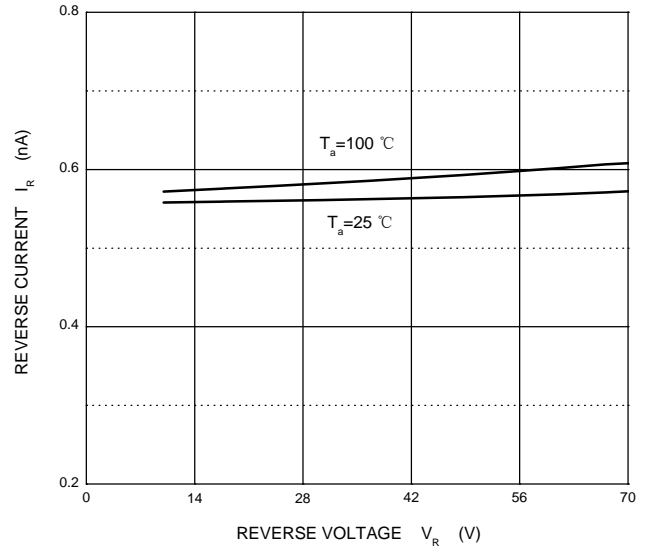
Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 100\mu A$	70		V
Reverse voltage leakage current	I_R	$V_R = 70V$		5	nA
Forward voltage	V_F	$I_F = 1mA$ $I_F = 10mA$ $I_F = 50mA$ $I_F = 150mA$		900 1000 1100 1250	mV
Diode capacitance	C_D	$V_R = 0, f = 1MHz$		2	pF
Reverse recovery time	t_{rr}	$I_F = I_R = 10mA$		3	μs

Typical Characteristics

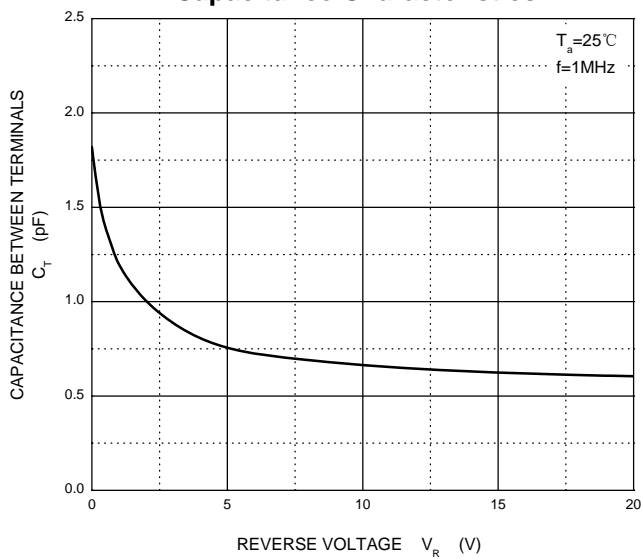
Forward Characteristics



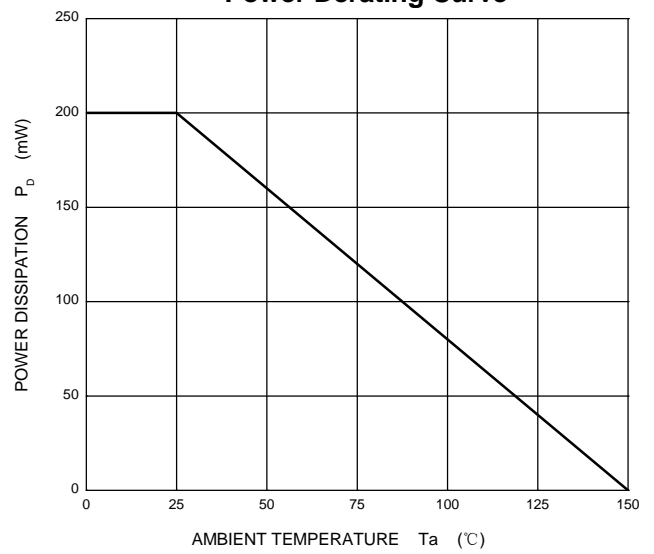
Reverse Characteristics

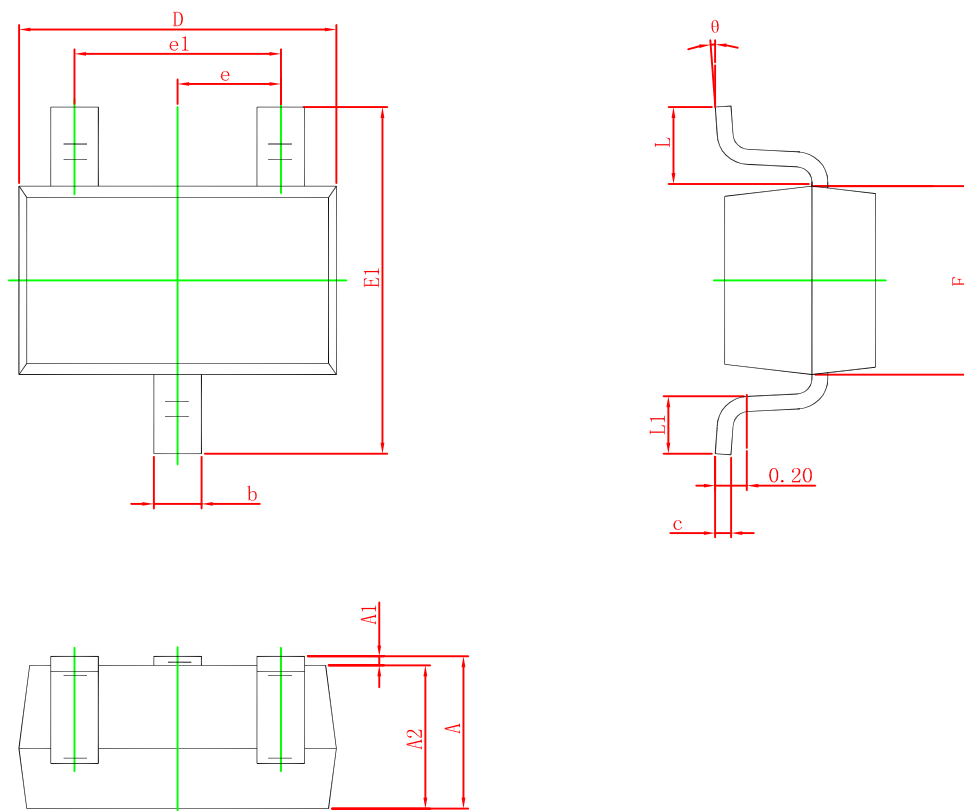


Capacitance Characteristics



Power Derating Curve



SOT-323 PACKAGE OUTLINE DIMENSIONS


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP.		0.026 TYP.	
e1	1.200	1.400	0.047	0.055
L	0.525 REF.		0.021 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°